

DYNAMIC CHARACTERISTICS

APT100S20LCT(G)

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
t_{rr}	Reverse Recovery Time	$I_F = 100A, di_F/dt = -200A/\mu s$ $V_R = 133V, T_C = 25^\circ C$	-	70		ns
Q_{rr}	Reverse Recovery Charge		-	230		nC
I_{RRM}	Maximum Reverse Recovery Current		-	6	-	Amps
t_{rr}	Reverse Recovery Time	$I_F = 100A, di_F/dt = -200A/\mu s$ $V_R = 133V, T_C = 125^\circ C$	-	110		ns
Q_{rr}	Reverse Recovery Charge		-	690		nC
I_{RRM}	Maximum Reverse Recovery Current		-	11	-	Amps
t_{rr}	Reverse Recovery Time	$I_F = 100A, di_F/dt = -700A/\mu s$ $V_R = 133V, T_C = 125^\circ C$	-	95		ns
Q_{rr}	Reverse Recovery Charge		-	1750		nC
I_{RRM}	Maximum Reverse Recovery Current		-	32		Amps

THERMAL AND MECHANICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction-to-Case Thermal Resistance			.18	$^\circ C/W$
W_T	Package Weight		0.22		oz
			5.9		g
Torque	Maximum Mounting Torque			10	lb•in
				1.1	N•m

Microsemi reserves the right to change, without notice, the specifications and information contained herein.

- ① Continuous current limited by package lead temperature.

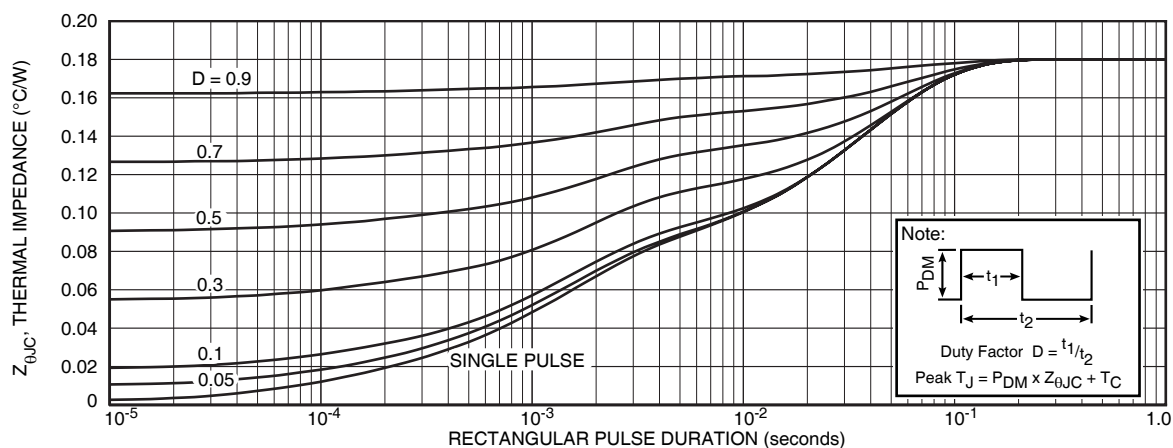


FIGURE 1a. MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs. PULSE DURATION

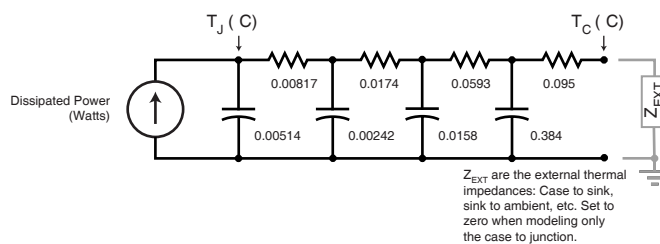


FIGURE 1b. TRANSIENT THERMAL IMPEDANCE MODEL

TYPICAL PERFORMANCE CURVES

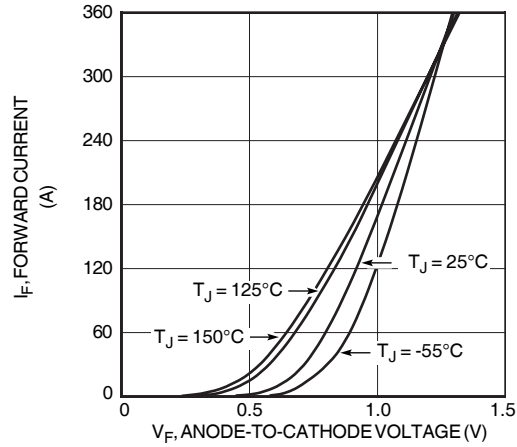


Figure 2. Forward Current vs. Forward Voltage

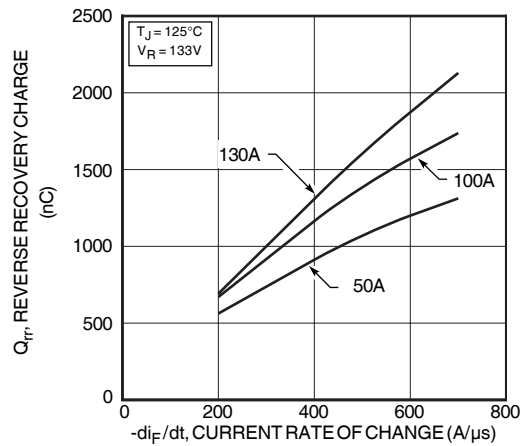


Figure 4. Reverse Recovery Charge vs. Current Rate of Change

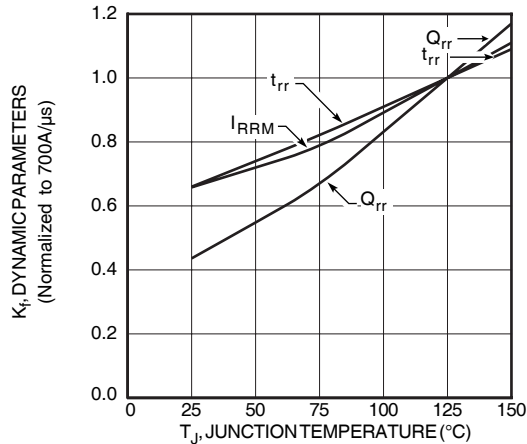


Figure 6. Dynamic Parameters vs. Junction Temperature

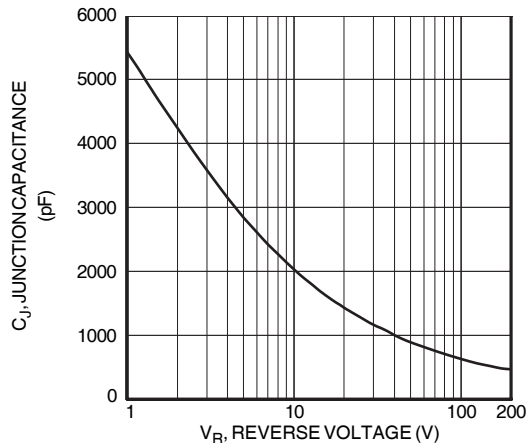


Figure 8. Junction Capacitance vs. Reverse Voltage

APT100S20LCT(G)

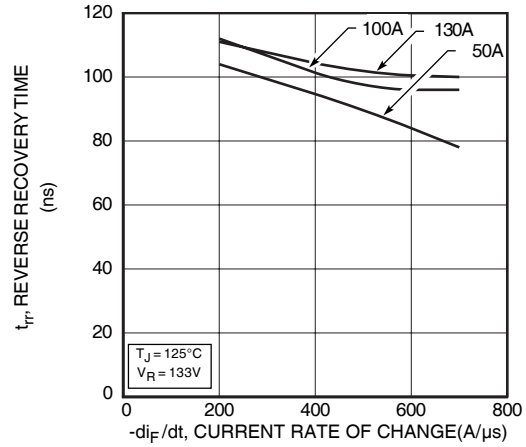


Figure 3. Reverse Recovery Time vs. Current Rate of Change

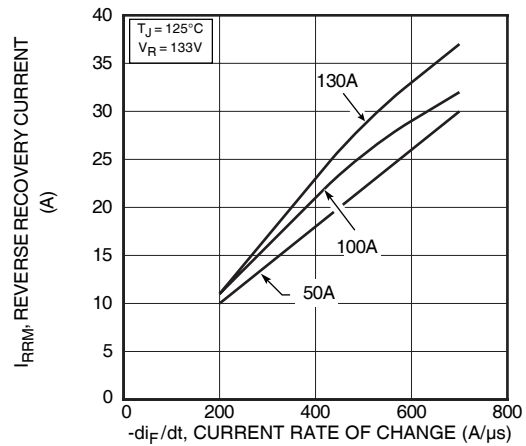


Figure 5. Reverse Recovery Current vs. Current Rate of Change

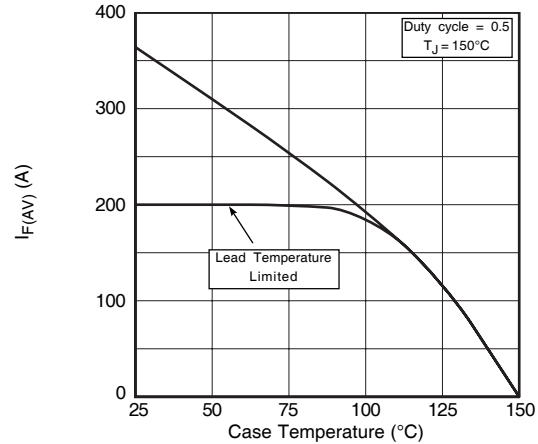


Figure 7. Maximum Average Forward Current vs. Case Temperature

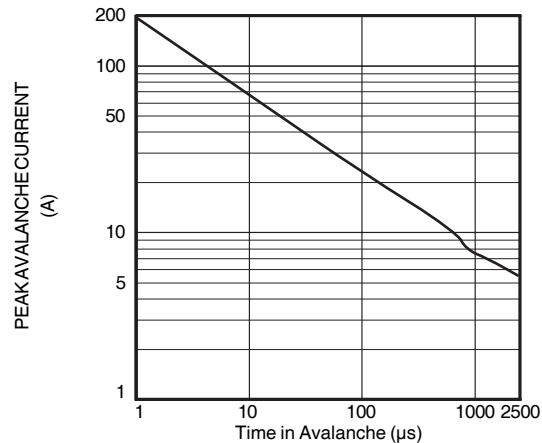


Figure 9. Single Pulse UIS SOA

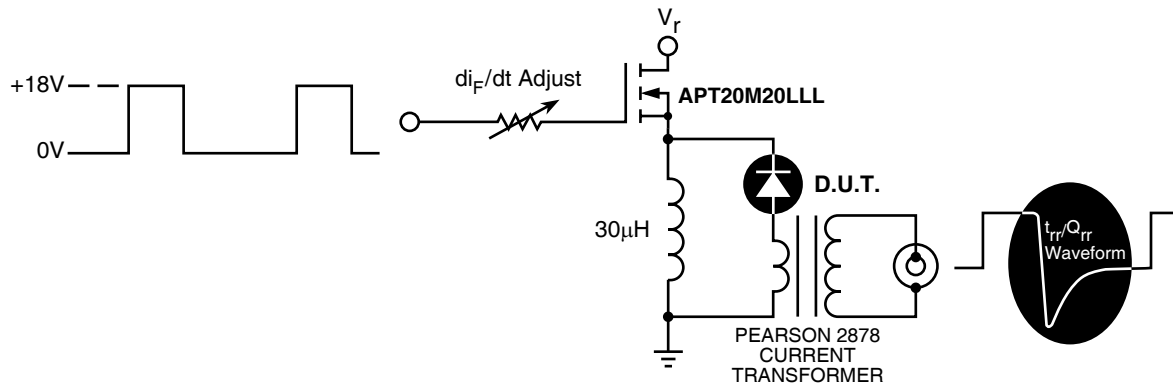


Figure 9. Diode Test Circuit

- 1 I_F - Forward Conduction Current
- 2 di_F/dt - Rate of Diode Current Change Through Zero Crossing.
- 3 I_{RRM} - Maximum Reverse Recovery Current.
- 4 t_{rr} - Reverse Recovery Time, measured from zero crossing where diode current goes from positive to negative, to the point at which the straight line through I_{RRM} and $0.25 \cdot I_{RRM}$ passes through zero.
- 5 Q_{rr} - Area Under the Curve Defined by I_{RRM} and t_{rr} .

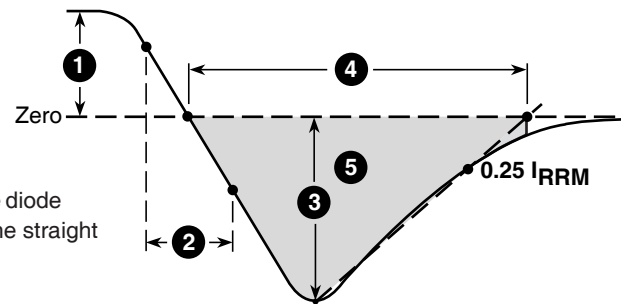


Figure 10. Diode Reverse Recovery Waveform and Definitions

TO-264 Package Outline

